CMOS Digital Integrated Circuits Silicon Monolithic

74HCT4051D,74HCT4052D

1. Functional Description

74HCT4051D:8-Channel Analog Multiplexer/Demultiplexer 74HCT4052D:Dual 4-Channel Analog Multiplexer/Demultiplexer

2. General

The 74HCT4051D/74HCT4052D are high speed CMOS ANALOG MULTIPLEXER/DEMULTIPLEXER fabricated with silicon gate C²MOS technology. They achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

This device may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. This inputs are compatible with TTL, NMOS and CMOS output voltage levels.

The 74HCT4051D has an 8 channel configuration and the 74HCT4052D has a 4 channel \times 2 configuration.

The digital signal to the control terminal turns "ON" the corresponding switch of each channel a large amplitude signal (V_{CC} - V_{EE}) can then be switched by the small logical amplitude (V_{CC} - GND) control signal.

For example, in the case of V_{CC} = 5 V, GND = 0 V, V_{EE} = -5 V, signals between -5 V and +5 V can be switched from the logical circuit with a single power supply of 5 V. As the ON-resistance of each switch is low, they can be connected to circuits with low input impedance.

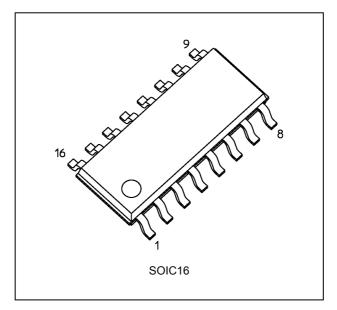
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

3. Features

- (1) Wide operating temperature range: $T_{\rm opr}$ = -40 to 125 °C (Note 1)
- (2) Low power dissipation: I_{CC} = 4.0 μ A (max) (V_{CC} = 5.5 V, V_{EE} = GND, T_a = 25 °C)
- (3) Compatible with TTL output: $V_{\rm IH}$ = 2.0 V (min), $V_{\rm IL}$ = 0.8 V (max)
- (4) Wide interfacing ability: LSTTL, NMOS, CMOS
- (5) Low ON-resistance: $R_{ON} = 50 \Omega$ (typ.) at $V_{CC} V_{EE} = 9 V$
- (6) High degree of linearity: THD = 0.020 % (typ.) at $V_{CC} V_{EE} = 9 V$

Note 1: Operating Range spec of T_{opr} = -40 °C to 125 °C is applicable only for the products which manufactured after July 2020.

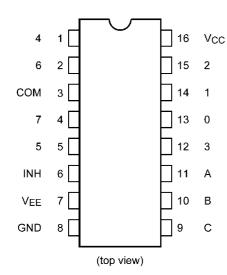
4. Packaging



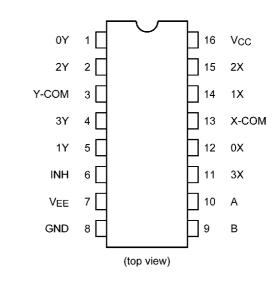
Start of commercial production 2020-07

5. Pin Assignment



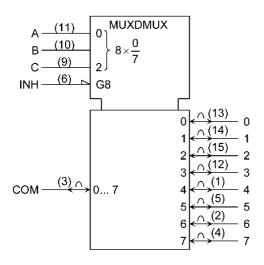


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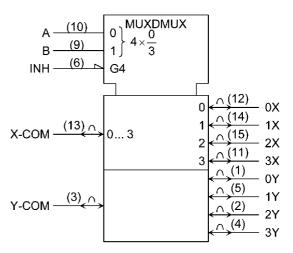


6. IEC Logic Symbol

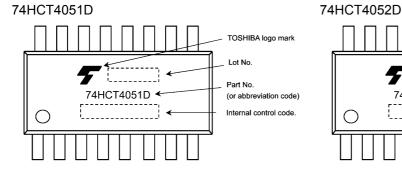
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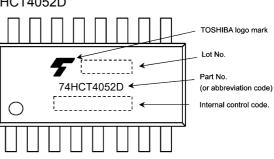


74HCT4052D



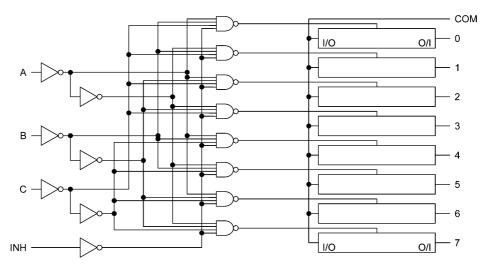
7. Marking



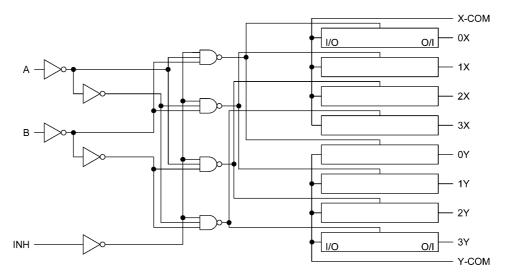


8. System Diagram

74HCT4051D



74HCT4052D



9. Truth Table

Input Inhibit	Input C*	Input B	Input A	ON Channel 74HCT4051D	ON Channel 74HCT4052D
L	L	L	L	0	0X, 0Y
L	L	L	Н	1	1X, 1Y
L	L	Н	L	2	2X, 2Y
L	L	Н	Н	3	3X, 3Y
L	Н	L	L	4	_
L	Н	L	Н	5	_
L	Н	Н	L	6	_
L	Н	Н	Н	7	_
Н	Х	Х	Х	None	None

X: Don't care

*: Except 74HCT4052D

10. Absolute Maximum Ratings (Note)

Characteristics	Symbol	Note	Rating	Unit
Supply voltage	V _{CC}		-0.5 to 7.0	V
Supply voltage	V _{EE}		-7.0 to 0	V
Supply voltage	V _{CC} -V _{EE}		-0.5 to 13.0	V
Input voltage	V _{IN}		-0.5 to V _{CC} + 0.5	V
Switch I/O voltage	V _{I/O}		V _{EE} - 0.5 to V _{CC} + 0.5	V
Input diode current	I _{IK}		±20	mA
I/O diode current	I _{I/OK}		±20	mA
Switch through current	Ι _Τ		±25	mA
V _{CC} /ground current	I _{CC}		±50	mA
Power dissipation	PD	(Note 1)	500	mW
Storage temperature	T _{stg}		-65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: P_D derates linearly with -8 mW/°C above 85 °C.

11. Operating Ranges (Note)

Characteristics	Symbol	Note	Rating	Unit
Supply voltage	V _{CC}		4.5 to 5.5	V
Supply voltage	V _{EE}		-6.0 to 0	V
Supply voltage	V _{CC} -V _{EE}		4.5 to 11.0	V
Input voltage	V _{IN}		0 to V _{CC}	V
Switch I/O voltage	V _{I/O}		V _{EE} to V _{CC}	V
Operating temperature	T _{opr}	(Note 1)	-40 to 125	°C
Input rise and fall times	t _r ,t _f		0 to 50	μS

Note: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either V_{CC} or GND.

Note 1: Operating Range spec of T_{opr} = -40 °C to 125 °C is applicable only for the products which manufactured after July 2020.

12. Electrical Characteristics

12.1. DC Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics	Symbol	Test Condition	V _{EE} (V)	V _{CC} (V)	Min	Тур.	Max	Unit
High-level input voltage	V _{IH}	—		4.5 to 5.5	2.0	—	—	V
Low-level input voltage	VIL	—		4.5 to 5.5	_	—	0.8	V
ON-resistance	R _{ON}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	GND	4.5	_	180	240	Ω
		$V_{I/O} = V_{CC}$ to V_{EE} $I_{I/O} \le 2 \text{ mA}$	-4.5	4.5		140	190	
			-5.5	5.5	_	135	180	
		$V_{IN} = V_{IH}$ or V_{IL}	GND	4.5		150	200	
		$V_{I/O} = V_{EE}$ $I_{I/O} \le 2 \text{ mA}$	-4.5	4.5		135	170	
			-5.5	5.5	_	125	170	
			GND	4.5	_	95	130	
			-4.5	4.5		75	100	
		$1/0 \ge 2 11/4$	-5.5	5.5		70	100	
Difference of ON-resistance	ΔR_{ON}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{I/O} = V_{CC} \text{ to } V_{EE}$ $I_{I/O} \le 2 \text{ mA}$	GND	4.5	_	10	30	Ω
between switches			-4.5	4.5		5	12	
			-5.5	5.5	_	5	11	
Input/Output leakage current	I _{OFF}	$V_{OS} = V_{CC}$ or GND	GND	5.5	_	—	±0.06	μA
(Switch OFF)		$V_{IS} = GND \text{ or } V_{CC}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	-5.5	5.5	_	—	±0.1	
Input/Output leakage current	I _{I/O}	V _{OS} = V _{CC} or GND	GND	5.5	_	—	±0.06	μA
(Switch ON)		$V_{IN} = V_{IH} \text{ or } V_{IL}$	-5.5	5.5			±0.1	
Control input leakage current	I _{IN}	V _{IN} = V _{CC} or GND	GND	5.5	_	_	±0.1	μA
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND	GND	5.5	_	_	4.0	μA
			-5.5	5.5			8.0	
		Per input: V_{IN} = 0.5 V or 2.4 V Other input: V _{CC} or GND	GND	5.5	_	—	2.0	mA

12.2. DC Characteristics (Unless otherwise specified, $T_a = -40$ to 85 °C)

Characteristics	Symbol	Test Condition	V _{EE} (V)	V _{CC} (V)	Min	Max	Unit
High-level input voltage	V _{IH}	—		4.5 to 5.5	2.0	_	V
Low-level input voltage	V _{IL}	—		4.5 to 5.5	_	0.8	V
ON-resistance	R _{ON}	V _{IN} = V _{IH} or V _{IL}	GND	4.5	_	300	Ω
		$V_{I/O} = V_{CC}$ to V_{EE} $I_{I/O} \le 2 \text{ mA}$	-4.5	4.5	_	240]
		II/0 ≤ 2 IIIA	-5.5	5.5	_	225	
		V _{IN} = V _{IH} or V _{IL}	GND	4.5	_	250]
		$V_{I/O} = V_{EE}$ $I_{I/O} \le 2 \text{ mA}$	-4.5	4.5	_	215	
		II/0 ≤ 2 IIIA	-5.5	5.5	_	215	
		V _{IN} = V _{IH} or V _{IL}	GND	4.5	_	165	
		$\begin{array}{l} V_{I/O} = V_{CC} \\ I_{I/O} \leq 2 \ mA \end{array}$	-4.5	4.5	_	125	
			-5.5	5.5	_	125	
Difference of ON-resistance	ΔR_{ON}	V _{IN} = V _{IH} or V _{IL}	GND	4.5	_	35	Ω
between switches		$V_{I/O} = V_{CC}$ to V_{EE} $I_{I/O} \le 2 \text{ mA}$	-4.5	4.5	_	15	
		II/0 ≤ 2 IIIA	-5.5	5.5	_	14	
Input/Output leakage current (Switch OFF)	I _{OFF}	$V_{OS} = V_{CC}$ or GND $V_{IS} = GND$ or V_{CC}	GND	5.5		±0.6	μΑ
		$V_{IN} = V_{IH} \text{ or } V_{IL}$	-5.5	5.5	_	±1.0	
Input/Output leakage current	I _{I/O}	V _{OS} = V _{CC} or GND	GND	5.5	_	±0.6	μA
(Switch ON)		$V_{IN} = V_{IH} \text{ or } V_{IL}$	-5.5	5.5	_	±1.0	
Control input leakage current	I _{IN}	V _{IN} = V _{CC} or GND	GND	5.5	_	±1.0	μA
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND	GND	5.5	_	40.0	μA
			-5.5	5.5	_	80.0	
		Per input: V _{IN} = 0.5 V or 2.4 V Other input: V _{CC} or GND	GND	5.5		2.9	mA

Characteristics	Symbol	Test Condition	V _{EE} (V)	V _{CC} (V)	Min	Max	Unit
High-level input voltage	V _{IH}	—		4.5 to 5.5	2.0	—	V
Low-level input voltage	VIL	—		4.5 to 5.5	_	0.8	V
ON-resistance	R _{ON}	V _{IN} = V _{IH} or V _{IL}	GND	4.5	_	340	Ω
		$V_{I/O} = V_{CC}$ to V_{EE} $I_{I/O} \le 2 \text{ mA}$	-4.5	4.5	_	275]
		$ /0 \ge 2 /4 $	-5.5	5.5	_	255	
		V _{IN} = V _{IH} or V _{IL}	GND	4.5	_	285]
		$V_{I/O} = V_{EE}$ $I_{I/O} \le 2 \text{ mA}$	-4.5	4.5	_	245]
		$ 1/0 \ge 2 11/4 $	-5.5	5.5	_	245]
		V _{IN} = V _{IH} or V _{IL}	GND	4.5	_	190	1
		$V_{I/O} = V_{CC}$	-4.5	4.5	_	145	
		$I_{I/O} \le 2 \text{ mA}$	-5.5	5.5	_	145	
Difference of ON-resistance	ΔR_{ON}	V _{IN} = V _{IH} or V _{IL}	GND	4.5	_	35	Ω
between switches		$V_{I/O} = V_{CC}$ to V_{EE} $I_{I/O} \le 2 \text{ mA}$	-4.5	4.5	_	15	
		$ 1 /0 \ge 2 1 /A$	-5.5	5.5	_	14	1
Input/Output leakage current	I _{OFF}	$V_{OS} = V_{CC}$ or GND	GND	5.5	_	±3.0	μΑ
(Switch OFF)		$V_{IS} = GND \text{ or } V_{CC}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	-5.5	5.5	_	±5.0]
Input/Output leakage current	I _{I/O}	V _{OS} = V _{CC} or GND	GND	5.5	_	±3.0	μΑ
(Switch ON)		$V_{IN} = V_{IH} \text{ or } V_{IL}$	-5.5	5.5	_	±5.0	1
Control input leakage current	I _{IN}	V _{IN} = V _{CC} or GND	GND	5.5	_	±1.0	μA
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND	GND	5.5	_	80.0	μA
			-5.5	5.5	_	160.0]
		Per input: V _{IN} = 0.5 V or 2.4 V Other input: V _{CC} or GND	GND	5.5	_	2.9	mA

12.3. DC Characteristics (Note) (Unless otherwise specified, T_a = -40 to 125 °C)

Note: Operating Range spec of T_{opr} = -40 °C to 125 °C is applicable only for the products which manufactured after July 2020.

12.4. AC Characteristics (Unless otherwise specified, $C_L = 50 \text{ pF}$, $T_a = 25 \text{ }^\circ\text{C}$, Input: $t_r = t_f = 6 \text{ ns}$)

Characteristics	Part Number	Symbol	Test Condition	V _{EE} (V)	V _{CC} (V)	Min	Тур.	Max	Unit
Phase difference		Φι/Ο	—	GND	4.5		7	12	ns
between input to output				GND	5.5	_	6	10	
				-4.5	4.5	—	5		
Output enable time	74HCT4051D	t _{PZL} ,t _{PZH}	$R_L = 1 k\Omega$	GND	4.5	—	30	45	ns
			Figure 1	GND	5.5		26	35	
				-4.5	4.5		25	35	
	74HCT4052D		$R_L = 1 k\Omega$	GND	4.5		30	45	ns
			Figure 1	GND	5.5		26	35	
				-4.5	4.5	_	25	35	
Output disable time	74HCT4051D	t _{PLZ} ,t _{PHZ}	R _L = 1 kΩ Figure 1	GND	4.5		22	30	ns
				GND	5.5	_	21	28	
				-4.5	4.5	_	21	28	
	74HCT4052D		$R_L = 1 k\Omega$	GND	4.5		22	30	ns
			Figure 1	GND	5.5	_	21	28	
				-4.5	4.5	_	21	28	
Control input capacitance		C _{IN}	_		_	—	5	10	pF
Common terminal	74HCT4051D	C _{IS}	Figure 2	-5.0	5.0		36	70	pF
capacitance	74HCT4052D					_	19	40]
Switch terminal	74HCT4051D	C _{OS}	Figure 2	-5.0	5.0		7	15	pF
capacitance	74HCT4052D					_	7	15	
Feedthrough	74HCT4051D	C _{IOS}	Figure 2	-5.0	5.0		0.75	2	pF
capacitance	74HCT4052D						0.75	2	
Power dissipation	74HCT4051D	C _{PD}	Figure 2	GND	5.0		11		pF
capacitance	74HCT4052D		(Note 1)				19		

Note 1: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation.

 $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$



12.5. AC Characteristics (Unless otherwise specified, C_L = 50 pF, T_a = -40 to 85 °C, Input: t_r = t_f = 6 ns)

Characteristics	Part Number	Symbol	Test Condition	V_{EE} (V)	V _{CC} (V)	Min	Max	Unit
Phase difference between		Φι/Ο	—	GND	4.5	_	15	ns
input to output				GND	5.5	_	13	
				-4.5	4.5	—		
Output enable time	74HCT4051D	t _{PZL} ,t _{PZH}	$R_L = 1 k\Omega$	GND	4.5	_	55	ns
			Figure 1	GND	5.5	_	42	
				-4.5	4.5	_	41	
	74HCT4052D		$R_L = 1 k\Omega$	GND	4.5	_	55	ns
			Figure 1	GND	5.5	_	42	
				-4.5	4.5	—	41	
Output disable time	74HCT4051D	$t_{\text{PLZ}}, t_{\text{PHZ}}$	$R_L = 1 k\Omega$	GND	4.5	—	37	ns
			Figure 1	GND	5.5	—	34	
				-4.5	4.5	—	34	
	74HCT4052D		$R_L = 1 k\Omega$	GND	4.5	—	37	ns
			Figure 1	GND	5.5	—	34	
				-4.5	4.5	—	34	
Control input capacitance		C _{IN}	—	—	—	—	10	pF
Common terminal	74HCT4051D	C _{IS}	Figure 2	-5.0	5.0	_	70	pF
capacitance	74HCT4052D					—	40	
Switch terminal capacitance	74HCT4051D	C _{OS}	Figure 2	-5.0	5.0	—	15	pF
	74HCT4052D					_	15	
Feedthrough capacitance	74HCT4051D	C _{IOS}	Figure 2	-5.0	5.0	_	2	pF
	74HCT4052D					—	2	

12.6. AC Characteristics (Note) (Unless otherwise specified, CL = 50 pF, $T_a = -40$ to 125 °C, Input: $t_r = t_f = 6$ ns)

Characteristics	Part Number	Symbol	Test Condition	V _{EE} (V)	V _{CC} (V)	Min	Max	Unit
Phase difference between		Φι/Ο	—	GND	4.5	_	17	ns
input to output				GND	5.0	_	15	1
				-4.5	4.5	_	_	1
Output enable time	74HCT4051D	t _{PZL} ,t _{PZH}	R _L = 1 kΩ	GND	4.5	_	62	ns
			Figure 1	GND	5.0	_	47	1
				-4.5	4.5	_	45]
	74HCT4052D		R _L = 1 kΩ	GND	4.5	_	62	ns
			Figure 1	GND	5.0	—	47	
				-4.5	4.5	_	45]
Output disable time	74HCT4051D	t _{PLZ} ,t _{PHZ}	R _L = 1 kΩ	GND	4.5	_	42	ns
	74HCT4052D		Figure 1 R _L = 1 kΩ Figure 1	GND	5.0	_	38	1
				-4.5	4.5	_	38]
				GND	4.5	_	42	ns
				GND	5.0	—	38]
				-4.5	4.5	_	38]
Control input capacitance		C _{IN}	_	—	—	—	10	pF
Common terminal	74HCT4051D	CIS	Figure 2	-5.0	5.0	—	70	pF
capacitance	74HCT4052D					_	40]
Switch terminal capacitance	74HCT4051D	C _{OS}	Figure 2	-5.0	5.0	_	15	pF
	74HCT4052D					_	15	
Feedthrough capacitance	74HCT4051D	C _{IOS}	Figure 2	-5.0	5.0	_	2	pF
	74HCT4052D					_	2	1

Note: Operating Range spec of T_{opr} = -40 °C to 125 °C is applicable only for the products which manufactured after July 2020.

12.7. Analog Switch Characteristics ($T_a = 25 \ ^{\circ}C$) (Note)

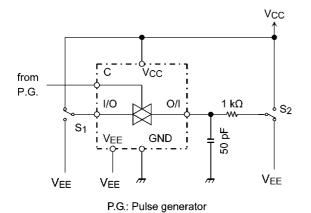
Characteristics	Part Number	Symbol	Test Condition		V _{EE} (V)	V _{CC} (V)	Тур.	Unit
Sine Wave Distortion		THD	R_L = 10 k Ω , C_L = 50 pF	V_{IN} = 8.0 V_{p-p}	-4.5	4.5	0.020	%
			f _{IN} = 1 kHz	V _{IN} = 11.0 V _{p-p}	-5.5	5.5	0.019	
Maximum frequency		f _{MAX(I/O)}	Adjust f _{IN} voltage to obtain	(Note 1)	-4.5	4.5	190	MHz
response	74HCT4051D		0 dBm at V _{OS} Increase f _{IN} frequency until	(Note 2)			70	
	74HCT4052D		dB meter reads -3 dB				110	
			$R_{L} = 50 \Omega, C_{L} = 10 pF$	(Note 1)	-5.5	5.5	200	
	74HCT4051D		Figure 3	(Note 2)			80	
	74HCT4052D						135	
Feed through attenuation (switch OFF)		FTH	V_{IN} is centered at ($V_{CC}/2$). Adjust input for 0 dBm.		-4.5	4.5	-50	dB
			$R_L = 600 \Omega$, $C_L = 50 pF$, $f_{IN} = 1 MHz$, sine wave Figure 4		-5.5	5.5	-50	
Crosstalk (control input to signal output)		X _{talk}	$R_L = 600 \Omega$, $C_L = 50 pF$, f _{IN} = 1 MHz,		-4.5	4.5	140	mV
			square wave (t _r = t _f = 6 ns) Figure 5		-5.5	5.5	180	
Crosstalk (between any switches)		X _{talk}	Adjust V _{IN} to obtain 0 dBm at input. $R_1 = 600 \Omega$, $C_1 = 50 pF$,		-4.5	4.5	-50	dB
			$f_{IN} = 1 \text{ MHz}$, sine wave Figure 6		-5.5	5.5	-50	
			R_L = 50 Ω, C_L = 15 pF, f_{IN} = 100 KHz, V_{SWITCH} = 1 V_{RMS} Figure 6		-4.5	4.5	-90	dB

Note: These characteristics are determined by design of devices.

Note 1: Input COMMON terminal, and measured at SWITCH terminal.

Note 2: Input SWITCH terminal, and measured at COMMON terminal.

13. AC Test Circuit



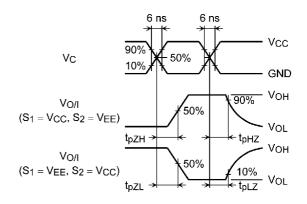


Figure 1 tPLZ, tPHZ, tPZL, tPZH

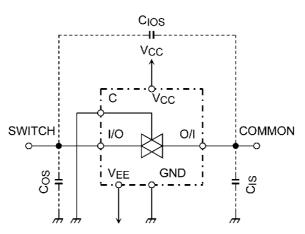


Figure 2 CIOS, CIS, COS

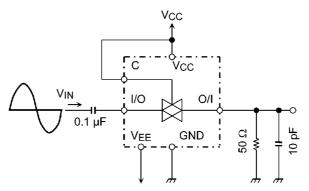


Figure 3 Frequency Response

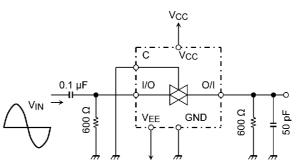
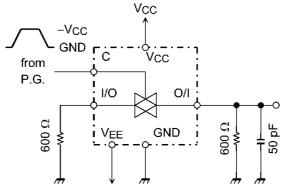
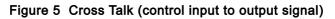


Figure 4 Feedthrough Attenuation



P.G.: Pulse generator



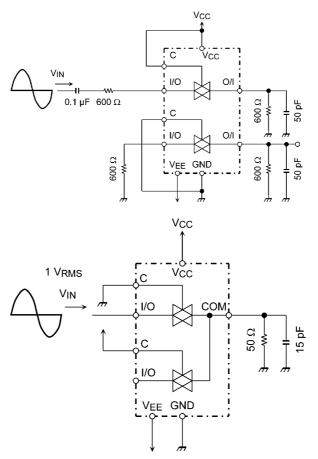


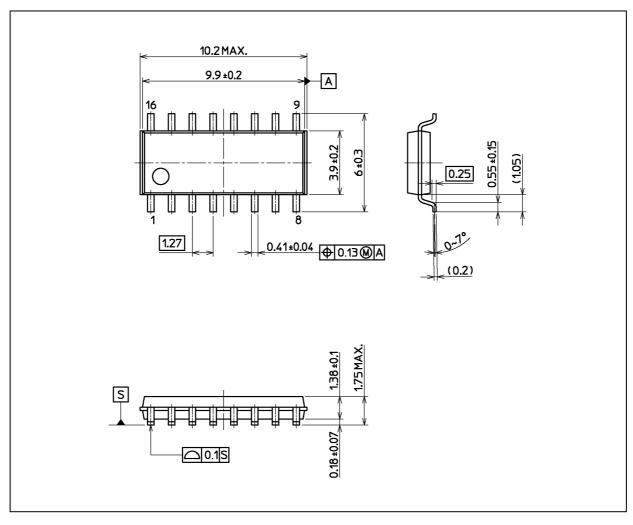
Figure 6 Cross Talk (between any two switches)



74HCT4051D,74HCT4052D

Package Dimensions

Unit: mm



Weight: 0.15 g (typ.)

Package Name(s)

Nickname: SOIC16

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